



## Description

The NVMFS5826NL uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = 60V$   $I_D = 30A$

$R_{DS(ON)} < 25m\Omega$  @  $V_{GS}=10V$

## Application

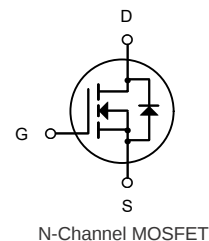
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L  
(SO-8-FL-5.8mm)



N-Channel MOSFET

## Package Marking and Ordering Information

| Product ID  | Pack                     | Brand      | Qty(PCS) |
|-------------|--------------------------|------------|----------|
| NVMFS5826NL | DFN5X6-8L(SO-8-FL-5.8mm) | HXY MOSFET | 5000     |

## Absolute Maximum Ratings ( $T_C=25^{\circ}C$ unless otherwise noted)

| Symbol                 | Parameter                                        | Rating     | Units         |
|------------------------|--------------------------------------------------|------------|---------------|
| $V_{DS}$               | Drain-Source Voltage                             | 60         | V             |
| $V_{GS}$               | Gate-Source Voltage                              | $\pm 20$   | V             |
| $I_D@T_C=25^{\circ}C$  | Continuous Drain Current, $V_{GS} @ 10V^1$       | 30         | A             |
| $I_D@T_C=100^{\circ}C$ | Continuous Drain Current, $V_{GS} @ 10V^1$       | 15         | A             |
| IDM                    | Pulsed Drain Current <sup>2</sup>                | 46         | A             |
| EAS                    | Single Pulse Avalanche Energy <sup>3</sup>       | 25.5       | mJ            |
| IAS                    | Avalanche Current                                | 22.6       | A             |
| $P_D@T_C=25^{\circ}C$  | Total Power Dissipation <sup>4</sup>             | 34.7       | W             |
| TSTG                   | Storage Temperature Range                        | -55 to 150 | $^{\circ}C$   |
| $T_J$                  | Operating Junction Temperature Range             | -55 to 150 | $^{\circ}C$   |
| $R_{\theta JA}$        | Thermal Resistance Junction-ambient <sup>1</sup> | 62         | $^{\circ}C/W$ |
| $R_{\theta JC}$        | Thermal Resistance Junction-Case <sup>1</sup>    | 3.6        | $^{\circ}C/W$ |



**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

| Symbol                     | Parameter                                      | Conditions                                                   | Min. | Typ.  | Max.      | Unit                |
|----------------------------|------------------------------------------------|--------------------------------------------------------------|------|-------|-----------|---------------------|
| $BV_{DSS}$                 | Drain-Source Breakdown Voltage                 | $V_{GS}=0V$ , $I_D=250\mu A$                                 | 60   | ---   | ---       | V                   |
| $\Delta BV_{DSS}/\Delta T$ | $BV_{DSS}$ Temperature Coefficient             | Reference to $25^\circ\text{C}$ , $I_D=1mA$                  | ---  | 0.063 | ---       | $V/^\circ\text{C}$  |
| $R_{DS(ON)}$               | Static Drain-Source On-Resistance <sup>2</sup> | $V_{GS}=10V$ , $I_D=15A$                                     | ---  | 20    | 25        | $m\Omega$           |
|                            |                                                | $V_{GS}=4.5V$ , $I_D=10A$                                    | ---  | 24    | 20        |                     |
| $V_{GS(th)}$               | Gate Threshold Voltage                         | $V_{GS}=V_{DS}$ , $I_D=250\mu A$                             | 1.2  | ---   | 2.5       | V                   |
| $\Delta V_{GS(th)}$        | $V_{GS(th)}$ Temperature Coefficient           |                                                              | ---  | -5.24 | ---       | $mV/^\circ\text{C}$ |
| $I_{DSS}$                  | Drain-Source Leakage Current                   | $V_{DS}=48V$ , $V_{GS}=0V$ , $T_J=25^\circ\text{C}$          | ---  | ---   | 1         | $\mu A$             |
|                            |                                                | $V_{DS}=48V$ , $V_{GS}=0V$ , $T_J=55^\circ\text{C}$          | ---  | ---   | 5         |                     |
| $I_{GSS}$                  | Gate-Source Leakage Current                    | $V_{GS}=\pm 20V$ , $V_{DS}=0V$                               | ---  | ---   | $\pm 100$ | nA                  |
| gfs                        | Forward Transconductance                       | $V_{DS}=5V$ , $I_D=15A$                                      | ---  | 17    | ---       | S                   |
| $R_g$                      | Gate Resistance                                | $V_{DS}=0V$ , $V_{GS}=0V$ , $f=1MHz$                         | ---  | 3.2   | ---       | $\Omega$            |
| $Q_g$                      | Total Gate Charge (4.5V)                       | $V_{DS}=48V$ , $V_{GS}=4.5V$ , $I_D=12A$                     | ---  | 12.6  | ---       | nC                  |
| $Q_{gs}$                   | Gate-Source Charge                             |                                                              | ---  | 3.2   | ---       |                     |
| $Q_{gd}$                   | Gate-Drain Charge                              |                                                              | ---  | 6.3   | ---       |                     |
| $T_{d(on)}$                | Turn-On Delay Time                             | $V_{DD}=30V$ , $V_{GS}=10V$ , $R_G=3.3\Omega$ ,<br>$I_D=10A$ | ---  | 8     | ---       | ns                  |
| $T_r$                      | Rise Time                                      |                                                              | ---  | 14.2  | ---       |                     |
| $T_{d(off)}$               | Turn-Off Delay Time                            |                                                              | ---  | 24.4  | ---       |                     |
| $T_f$                      | Fall Time                                      |                                                              | ---  | 4.6   | ---       |                     |
| $C_{iss}$                  | Input Capacitance                              | $V_{DS}=15V$ , $V_{GS}=0V$ , $f=1MHz$                        | ---  | 1378  | ---       | pF                  |
| $C_{oss}$                  | Output Capacitance                             |                                                              | ---  | 86    | ---       |                     |
| $C_{rss}$                  | Reverse Transfer Capacitance                   |                                                              | ---  | 64    | ---       |                     |

**Diode Characteristics**

| Symbol   | Parameter                                | Conditions                                      | Min. | Typ. | Max. | Unit |
|----------|------------------------------------------|-------------------------------------------------|------|------|------|------|
| $I_S$    | Continuous Source Current <sup>1,5</sup> | $V_G=V_D=0V$ , Force Current                    | ---  | ---  | 30   | A    |
| $I_{SM}$ | Pulsed Source Current <sup>2,5</sup>     |                                                 | ---  | ---  | 46   | A    |
| $V_{SD}$ | Diode Forward Voltage <sup>2</sup>       | $V_{GS}=0V$ , $I_S=1A$ , $T_J=25^\circ\text{C}$ | ---  | ---  | 1.2  | V    |

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V$ ,  $V_{GS}=10V$ ,  $L=0.1mH$ ,  $I_{AS}=22.6A$
- 4.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



## Typical Characteristics

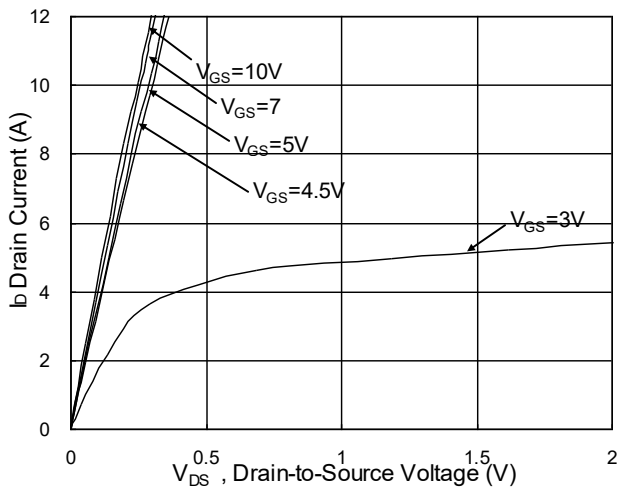


Fig.1 Typical Output Characteristics

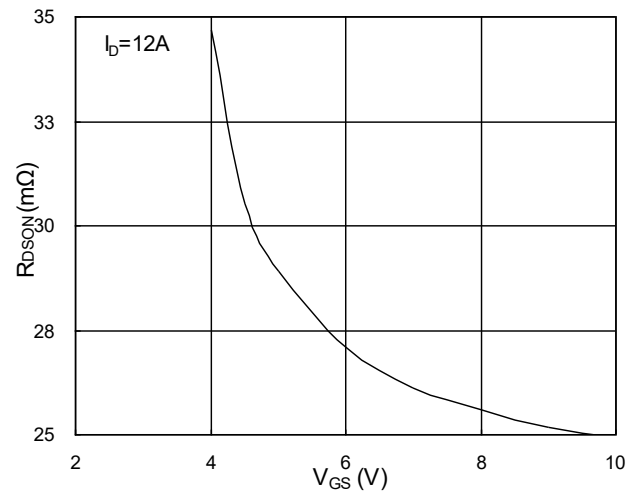


Fig.2 On-Resistance v.s Gate-Source

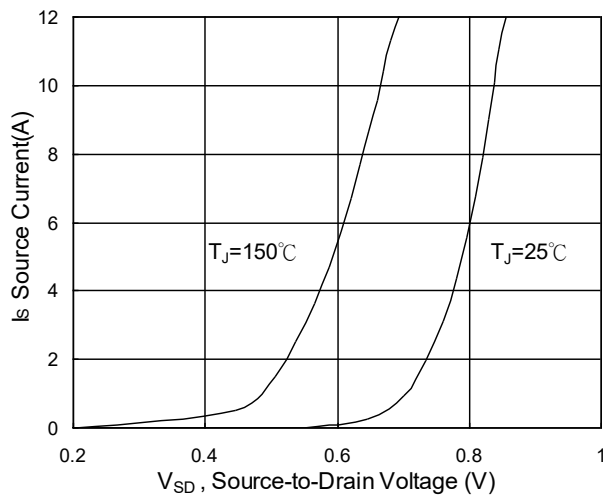


Fig.3 Forward Characteristics of Reverse

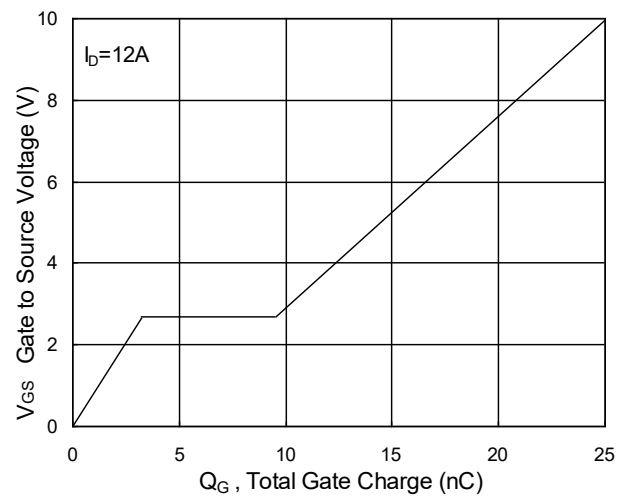


Fig.4 Gate-Charge Characteristics

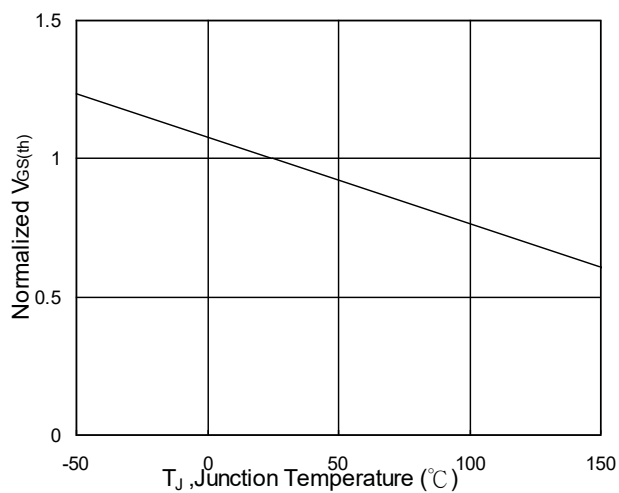


Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$

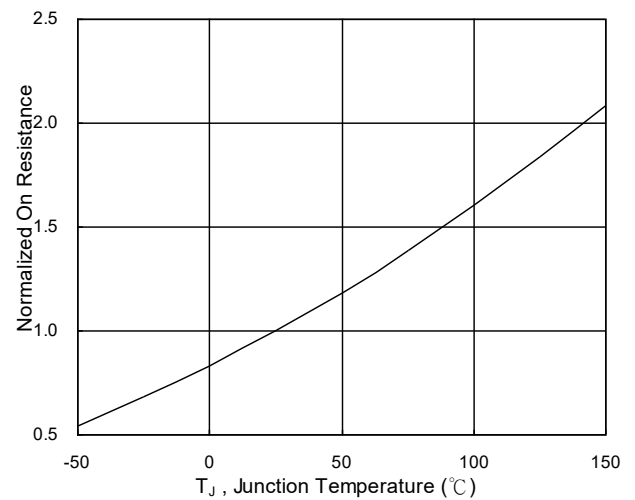


Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$

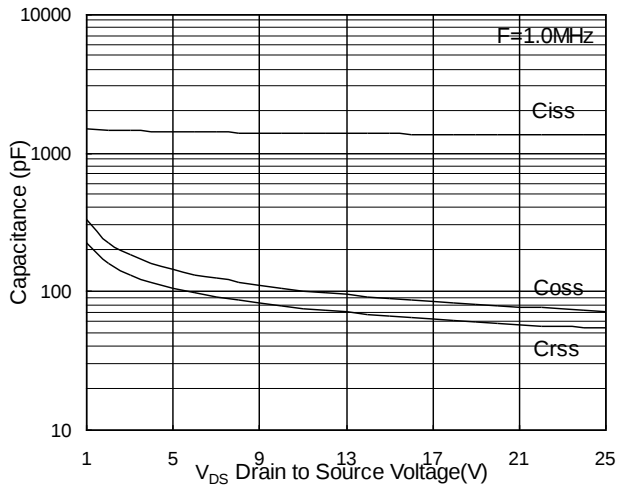


Fig.7 Capacitance

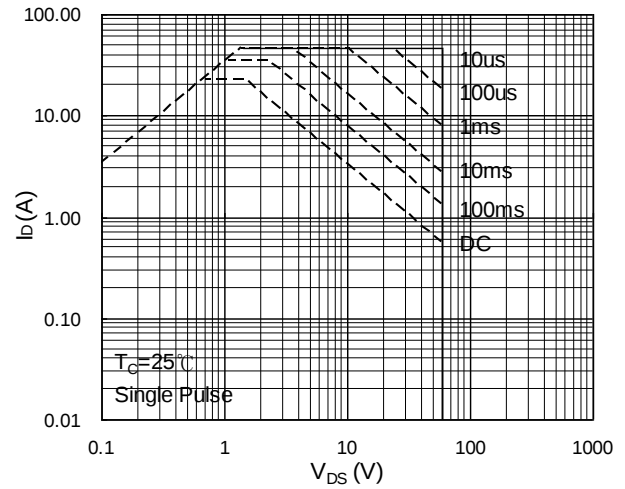


Fig.8 Safe Operating Area

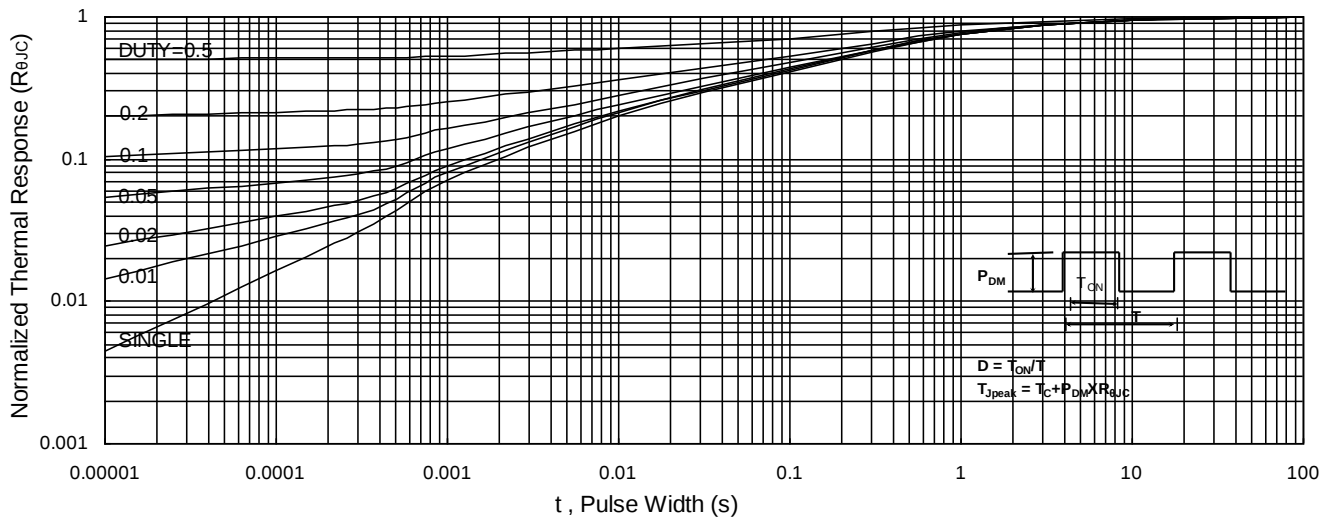


Fig.9 Normalized Maximum Transient Thermal Impedance

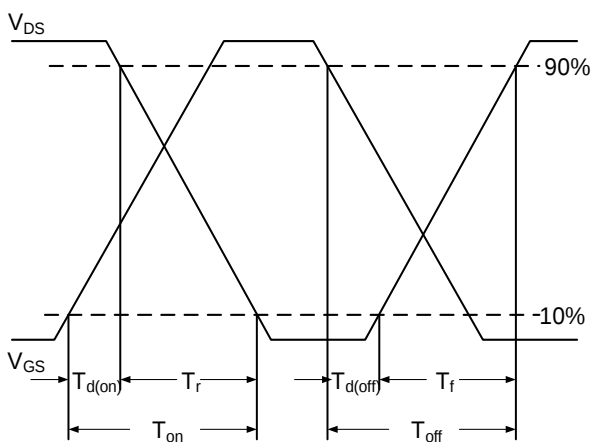


Fig.10 Switching Time Waveform

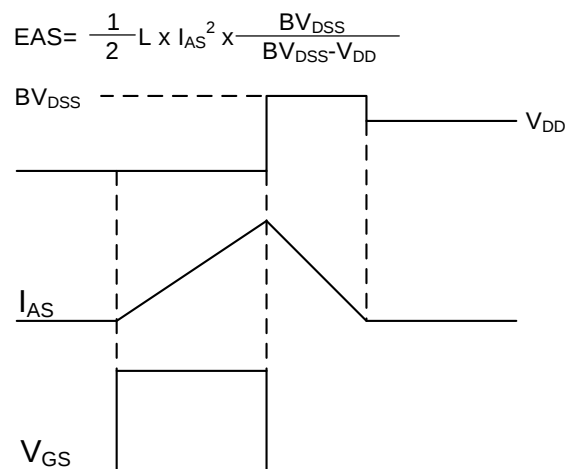
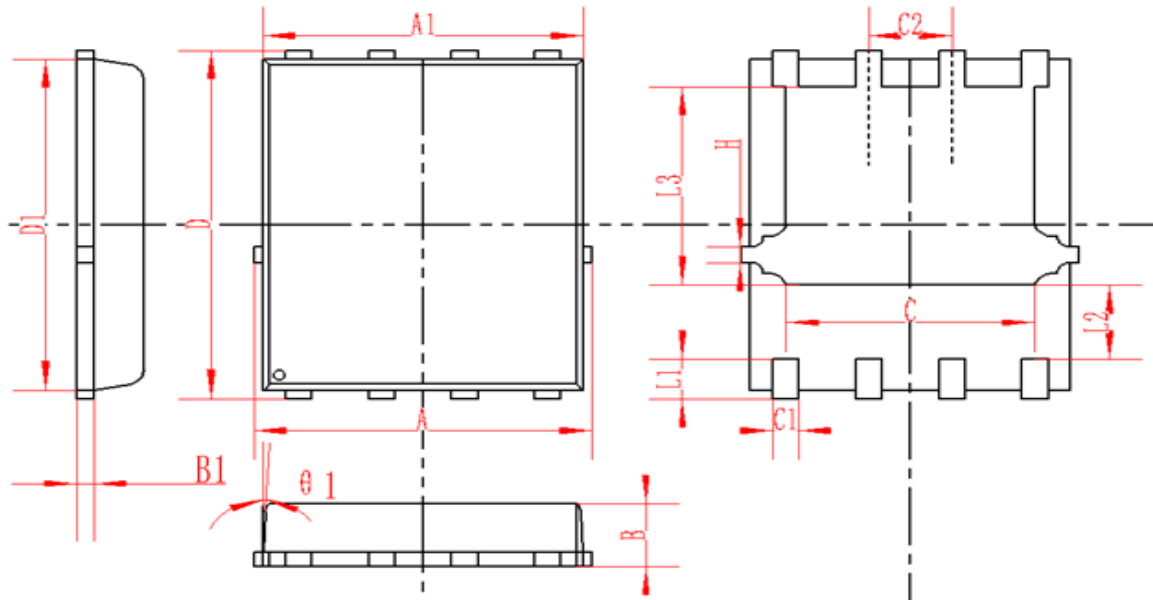


Fig.11 Unclamped Inductive Waveform



### DFN5X6-8L(SO-8-FL-5.8mm) Package Information



| SYMBOL | MM       |      |       | INCH     |       |       |
|--------|----------|------|-------|----------|-------|-------|
|        | MIN      | NOM  | MAX   | MIN      | NOM   | MAX   |
| A      | 4.95     | 5    | 5.05  | 0.195    | 0.197 | 0.199 |
| A1     | 4.82     | 4.9  | 4.98  | 0.190    | 0.193 | 0.196 |
| D      | 5.98     | 6    | 6.02  | 0.235    | 0.236 | 0.237 |
| D1     | 5.67     | 5.75 | 5.83  | 0.223    | 0.226 | 0.230 |
| B      | 0.9      | 0.95 | 1     | 0.035    | 0.037 | 0.039 |
| B1     | 0.254REF |      |       | 0.010REF |       |       |
| C      | 3.95     | 4    | 4.05  | 0.156    | 0.157 | 0.159 |
| C1     | 0.35     | 0.4  | 0.45  | 0.014    | 0.016 | 0.018 |
| C2     | 1.27TYP  |      |       | 0.5TYP   |       |       |
| θ1     | 8°       | 10°  | 12°   | 8°       | 10°   | 12°   |
| L1     | 0.63     | 0.64 | 0.65  | 0.025    | 0.025 | 0.026 |
| L2     | 1.2      | 1.3  | 1.4   | 0.047    | 0.051 | 0.055 |
| L3     | 3.415    | 3.42 | 3.425 | 0.134    | 0.135 | 0.135 |
| H      | 0.24     | 0.25 | 0.26  | 0.009    | 0.010 | 0.010 |



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